## FEATURE

- HIGH FREQUENCY SWITCHING - 200 kHz
- WIDE SUPPLY RANGE-16-200V
- 15A CONTINUOUS TO $65^{\circ}$ C CASE
- 3 PROTECTION CIRCUITS
- ANALOG OR DIGITAL INPUTS
- SYNCHRONIZED OR EXTERNAL OSCILLATOR
- FLEXIBLE FREQUENCY CONTROL


## APPLICATIONS

- reactive loads
- LOW FREQUENCY SONAR
- LARGE PIEZO ELEMENTS
- OFF-LINE DRIVERS
- C-D WELD CONTROLLER


## DESCRIPTION

The SA12 is a pulse width modulation amplifier that can supply 3000 W to the load. An internal 400 kHz oscillator requires no external components. The clock input stage divides the oscillator frequency by two, which provides the 200 kHz switching frequency. External oscillators may also be used to lower the switching frequency or to synchronize multiple amplifiers. Current sensing is provided for each half of the H -bridge giving amplitude and direction data. A shutdown input turns off all four drivers of the H -bridge output. A high side current limit and the programmable low side current limit protect the amplifier from shorts to supply or ground in addition to load shorts. The H-bridge output MOSFETs are protected from thermal overloads by directly sensing the temperature of the die. The 12 -pin hermetic MO-127 power package occupies only 3 square inches of board space.

## BLOCK DIAGRAM AND TYPICAL APPLICATION



## ABSOLUTE MAXIMUM RATINGS

| SUPPLY VOLTAGE, $+\mathrm{V}_{\mathrm{s}}$ | 200 V |
| :--- | :--- |
| SUPPLY VOLTAGE, $\mathrm{V}_{\mathrm{cc}}$ | 16 V |
| POWER DISSIPATION, internal | $250 \mathrm{~W}^{1}$ |
| TEMPERATURE, pin solder - 10 s | $300^{\circ} \mathrm{C}$ |
| TEMPERATURE, junction ${ }^{3}$ | $150^{\circ} \mathrm{C}$ |
| TEMPERATURE, storage | -65 to $+150^{\circ} \mathrm{C}$ |
| OPERATING TEMPERATURE RANGE, case | -55 to $+125^{\circ} \mathrm{C}$ |
| INPUT VOLTAGE, +PWM | 0 to +11 V |
| INPUT VOLTAGE, |  |
| INWM | 0 to +11 V |
| INUT VOLTAGE, LIM | 0 to +10 V |

## SPECIFICATIONS

| PARAMETER | TEST CONDITIONS ${ }^{2}$ | MIN | TYP | MAX | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: |
| CLOCK (CLK) |  |  |  |  |  |
| CLK OUT, high level ${ }^{4}$ | $\mathrm{I}_{\text {OUT }} \leq 1 \mathrm{~mA}$ | 4.8 |  | 5.3 | V |
| CLK OUT, low level ${ }^{4}$ | $\mathrm{l}_{\text {OUT }} \leq 1 \mathrm{~mA}$ | 0 |  | . 4 | V |
| FREQUENCY |  | 392 | 400 | 408 | kHz |
| RAMP, center voltage |  |  | 5 |  | V |
| RAMP, P-P voltage |  |  | 4 |  | V |
| CLK IN, low level ${ }^{4}$ |  | 0 |  | . 9 | V |
| CLK IN, high level ${ }^{4}$ |  | 3.7 |  | 5.4 | V |
| OUTPUT |  |  |  |  |  |
| TOTAL R ${ }_{\text {ON }}{ }^{4}$ |  |  |  | . 4 | $\Omega$ |
| EFFICIENCY, 10A output | $\mathrm{V}_{\mathrm{S}}=200 \mathrm{~V}$ |  | 97 |  | \% |
| SWITCHING FREQUENCY | OSC in $\div 2$ | 196 | 200 | 204 | kHz |
| CURRENT, continuous ${ }^{4}$ | $65^{\circ} \mathrm{C}$ case | 15 |  |  | A |
| CURRENT, peak ${ }^{4}$ |  | 20 |  |  | A |
| POWER SUPPLY |  |  |  |  |  |
| VOLTAGE, V ${ }_{\text {S }}$ | Full temperature range | 16 | 120 | 200 | V |
| VOLTAGE, V ${ }_{\text {cc }}$ | Full temperature range | 14 | 15 | 16 | V |
| CURRENT, $\mathrm{V}_{\text {cc }}$ | $\mathrm{l}_{\text {OUT }}=0$ |  |  | 80 | mA |
| CURRENT, $\mathrm{V}_{\mathrm{cc}}$, shutdown |  |  |  | 50 | mA |
| CURRENT, V | No Load |  |  | 200 | mA |
| $\mathrm{ILIM}^{\text {/SHUTDOWN }}$ |  |  |  |  |  |
| TRIP POINT |  | 90 |  | 110 | mV |
| INPUT CURRENT |  |  |  | 100 | nA |
| THERMAL ${ }^{3}$ |  |  |  |  |  |
| RESISTANCE, junction to case | Full temperature range, for each die |  |  | 1 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| RESISTANCE, junction to air | Full temperature range |  | 12 |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| TEMPERATURE RANGE, case | Meets full range specifications | -25 |  | +85 | ${ }^{\circ} \mathrm{C}$ |

NOTES: 1. Each of the two active output transistors can dissipate 125W.
2. Unless otherwise noted: $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{S}}, \mathrm{V}_{\mathrm{CC}}$ at typical specification.
3. Long term operation at the maximum junction temperature will result in reduced product life. Derate internal power dissipation to achieve high MTTF. For guidance, refer to the heatsink data sheet.
4. Guaranteed but not tested.

## CAUTION

The SA12 is constructed from MOSFET transistors. ESD handling procedures must be observed.
The internal substrate contains beryllia ( BeO ). Do not break the seal. If accidentally broken, do not crush, machine, or subject to temperatures in excess of $850^{\circ} \mathrm{C}$ to avoid generating toxic fumes.


OPERATING CONSIDERATIONS

## GENERAL

Helpful information about power supplies, heatsinking and mounting can be found in the "General Operating Considerations" section of the Apex data book. For information on the package outline, heatsinks, and mounting hardware see the "Package Outlines" and "Accessories" section of the data book. Also see Application Note 30 on "PWM Basics."

## CLOCK CIRCUIT AND RAMP GENERATOR

The clock frequency is internally set to a frequency of approximately 400 kHz . The CLK OUT pin will normally be tied to the CLK IN pin. The clock is divided by two and applied to an RC network which produces a ramp signal at the -PWM/ RAMP pin. An external clock signal can be applied to the CLK IN pin for synchronization purposes. If a clock frequency lower than 400 kHz is chosen an external capacitor must be tied to the -PWM/RAMP pin. This capacitor, which parallels an internal capacitor, must be selected so that the ramp oscillates 4 volts $p-p$ with the lower peak 3 volts above ground.

## PWM INPUTS

The full bridge driver may be accessed via the pwm input comparator. When +PWM > -PWM then A OUT > B OUT. A motion control processor which generates the pwm signal can drive these pins with signals referenced to GND.

## PROTECTION CIRCUITS

A fixed internal current limit senses the high side current. Should either of the outputs be shorted to ground the high side current limit will latch off the output transistors. The temperature of the output transistors is also monitored. Should a fault condition raise the temperature of the output transistors to $165^{\circ} \mathrm{C}$ the thermal protection circuit will latch off the output transistors. The latched condition can be cleared by either recycling the $\mathrm{V}_{\mathrm{cc}}$ power or by toggling the I LIMIT/SHDN input with a 10 V pulse. See Figures A and B . The outputs will remain off as long as the shutdown pulse is high (10V).

## CURRENT LIMIT

There are two load current sensing pins, I SENSE A and I SENSE B. The two pins can be shorted in the voltage mode connection but both must be used in the current mode connection (see figures $A$ and $B$ ). It is recommended that $R_{\text {LIMIT }}$ resistors be non-inductive. Load current flows in the I SENSE pins. To avoid errors due to lead lengths connect the I LIMIT/ SHDN pin directly to the $\mathrm{R}_{\text {LIMIT }}$ resistors (through the filter network and shutdown divider resistor) and connect the $\mathrm{R}_{\text {LIMIT }}$ resistors directly to the GND pin.

Switching noise spikes will invariably be found at the I SENSE pins. The noise spikes could trip the current limit threshold which is only 100 mV . $\mathrm{R}_{\text {FILTER }}$ and $\mathrm{C}_{\text {FILTER }}$ should be adjusted so as to reduce the switching noise well below 100 mV to prevent false current limiting. The sum of the DC level plus the noise


FIGURE A. CURRENT LIMIT WITH SHUTDOWN VOLTAGE MODE.


The required value of $\mathrm{R}_{\text {LIIIT }}$ in voltage mode may be calculated by:

$$
\mathrm{R}_{\text {LIMIT }}=.1 \mathrm{~V} / \mathrm{I}_{\text {LIMIT }}
$$

where $R_{\text {LIMIT }}$ is the required resistor value, and $I_{\text {LIMIT }}$ is the maximum desired current. In current mode the required value of each $R_{\text {LIMIT }}$ is 2 times this value since the sense voltage is divided down by 2 (see Figure $B$ ). If $R_{\text {SHDN }}$ is used it will further divide down the sense voltage. The shutdown divider network will also have an effect on the filtering circuit.

## BYPASSING

Adequate bypassing of the power supplies is required for proper operation. Failure to do so can cause erratic and low efficiency operation as well as excessive ringing at the outputs. The Vs supply should be bypassed with at least a $1 \mu \mathrm{~F}$ ceramic capacitor in parallel with another low ESR capacitor of at least $10 \mu \mathrm{~F}$ per amp of output current. Capacitor types rated for switching applications are the only types that should be considered. The bypass capacitors must be physically connected directly to the power supply pins. Even one inch of lead length will cause excessive ringing at the outputs. This is due to the very fast switching times and the inductance of the lead connection. The bypassing requirements of the Vcc supply are less stringent, but still necessary. A $.1 \mu \mathrm{~F}$ to $.47 \mu \mathrm{~F}$ ceramic capacitor connected directly to the Vcc pin will suffice.

## MODULATION RANGE

The high side of the all N channel H -bridge is driven by a bootstrap circuit. For the output circuit to switch high, the low side circuit must have previously been switched on in order to charge the bootstrap capacitor. Therefore, if the input signal to the SA12 demands a 100\% duty cycle upon start-up the output will not follow and will be in a tri-state (open) condition. The ramp signal must cross the input signal at some point to correctly determine the output state. After the ramp crosses the input signal one time the output state will be correct thereafter. In addition, if during normal operation the input signal drives the SA12 beyond its linear modulation range (approximately $95 \%$ ) the output will jump to $100 \%$ modulation.

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[^0]:    This data sheet has been carefully checked and is believed to be reliable, however, no responsibility is assumed for possible inaccuracies or omissions. All specifications are subject to change without notice. SA12U REV. C DECEMBER 1999 © 1999 Apex Microtechnology Corp.

